

Appl. No. 10/044,271  
Amtd. Dated Dec. 14, 2005  
Reply to Advisory Action of Nov. 16, 2005

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1-3 (canceled)

Claim 4 (currently amended): ~~The method as described in claim 1, A method for making a thin film filter having a negative temperature drift coefficient, comprising the steps of:~~

providing a film stack material;

providing a substrate wafer which has a coefficient of thermal expansion greater than that of the film stack material;

polishing the substrate wafer;

depositing thin film layers made of the film stack material on the substrate wafer at a temperature substantially higher than room temperature, thereby creating a film stack on the substrate wafer;

cooling the substrate wafer-film stack laminate to room temperature;  
and

cutting the cooled substrate wafer-film stack laminate into pieces,  
wherein the coefficient of thermal expansion of the substrate wafer is within the range from  $10 \times 10^{-6}/^{\circ}\text{K}$  to  $20 \times 10^{-6}/^{\circ}\text{K}$ , and the substrate is made of a  $\text{SiO}_2\text{-Na}_2\text{O}\text{-K}_2\text{O}\text{-Li}_2\text{O}\text{-PbO}\text{-XO}_2$  system, wherein X can be titanium (Ti) or zirconium (Zr).

Claim 5 (currently amended): ~~The method as described in claim 1, A method for making a thin film filter having a negative temperature drift~~

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coefficient, comprising the steps of:

providing a film stack material;

providing a substrate wafer which has a coefficient of thermal expansion greater than that of the film stack material;

polishing the substrate wafer;

depositing thin film layers made of the film stack material on the substrate wafer at a temperature substantially higher than room temperature, thereby creating a film stack on the substrate wafer;

cooling the substrate wafer-film stack laminate to room temperature;

and

cutting the cooled substrate wafer-film stack laminate into pieces,  
wherein the coefficient of thermal expansion of the substrate wafer is within the range from  $10 \times 10^{-6}/^{\circ}\text{K}$  to  $20 \times 10^{-6}/^{\circ}\text{K}$ , and the substrate is made of a  $\text{SiO}_2\text{-Na}_2\text{O}\text{-K}_2\text{O}\text{-Li}_2\text{O}\text{-PbO}\text{-Q}_2\text{O}_3$  system wherein Q can be aluminum (Al).

Claim 6 (currently amended): The method as described in claim 1, A method for making a thin film filter having a negative temperature drift coefficient, comprising the steps of:

providing a film stack material;

providing a substrate wafer which has a coefficient of thermal expansion greater than that of the film stack material;

polishing the substrate wafer;

depositing thin film layers made of the film stack material on the substrate wafer at a temperature substantially higher than room temperature, thereby creating a film stack on the substrate wafer;

cooling the substrate wafer-film stack laminate to room temperature;

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and

cutting the cooled substrate wafer-film stack laminate into pieces,  
wherein the coefficient of thermal expansion of the substrate wafer  
is within the range from  $10 \times 10^{-6}/^{\circ}\text{K}$  to  $20 \times 10^{-6}/^{\circ}\text{K}$ , and the substrate is  
made of a  $\text{SiO}_2\text{-Na}_2\text{O}\text{-K}_2\text{O}\text{-Li}_2\text{O}\text{-P}_2\text{O}_5\text{-ZO}_2$  system, wherein Z can be  
titanium (Ti) or zirconium (Zr).

Claim 7 (currently amended): The method as described in claim 1, A  
method for making a thin film filter having a negative temperature drift  
coefficient, comprising the steps of:

providing a film stack material;

providing a substrate wafer which has a coefficient of thermal  
expansion greater than that of the film stack material;

polishing the substrate wafer;

depositing thin film layers made of the film stack material on the  
substrate wafer at a temperature substantially higher than room  
temperature, thereby creating a film stack on the substrate wafer;

cooling the substrate wafer-film stack laminate to room temperature;  
and

cutting the cooled substrate wafer-film stack laminate into pieces,  
wherein the coefficient of thermal expansion of the substrate wafer  
is within the range from  $10 \times 10^{-6}/^{\circ}\text{K}$  to  $20 \times 10^{-6}/^{\circ}\text{K}$ , and the substrate  
wafer is doped with at least one of a group comprising lead (Pb), lithium  
(Li), sodium (Na), and potassium (K).

Claim 8-18 (canceled)

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**Remarks****Claim Rejections Under 35 U.S.C. 102**

Claims 1, 3, 9 and 10 remain rejected under 35 U.S.C. 102(e) as being unpatentable over Scobey et al. (US 6,798,553).

In response to the Advisory action, applicants hereby cancel claims 1, 3, 9 and 10 without prejudice in order to place the instant application in a condition for allowance.

**Claim Rejections Under 35 U.S.C. 103**

Claim 8 remains rejected under 35 U.S.C. 103(a) as being unpatentable over Scobey et al. (US 6,798,553).

In response to the Advisory action, applicants hereby cancel claim 8 without prejudice in order to place the instant application in a condition for allowance.

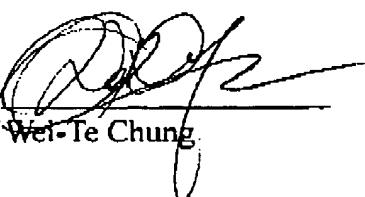
**Claim Objections**

Claims 4-7 remain objected as being dependent upon a rejected base claim.

In response to the Advisory action, applicants have rewritten claims 4-7 in independent form including all the limitations of the base claim. Applicants refer to the remarks under Allowable Subject Matter on p.3 of the Office action mailed Sep. 14, 2005, and submit that the objections are now overcome. Removal of the objections and allowance of claims 4-7 are requested.

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Respectfully submitted,  
Chen et al.

By



Wei-Te Chung

Registration No.: 43,325  
Foxconn International, Inc.  
P.O. Address: 1650 Memorex Drive, Santa Clara, CA 95050  
Tel. No.: (408) 919-6137